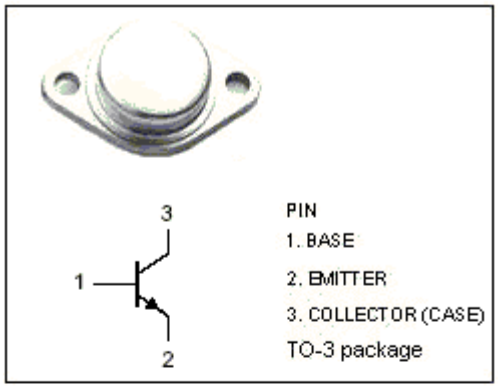
isc Silicon NPN Power Transistor 2N1470

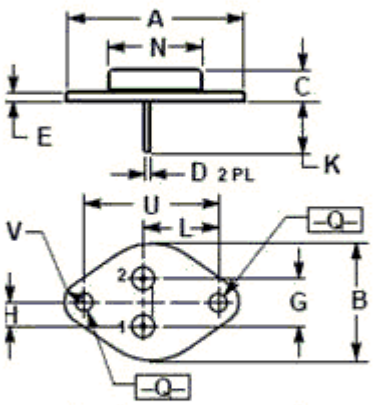


DESCRIPTION

- Excellent Safe Operating Area
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 1.0V(Max)@ I_C = 1.5A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 60V(Min)

APPLICATIONS

- Designed for general purpose amplifier and switching applications.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	3	A
P_C	Collector Power Dissipation@T_C=25℃	55	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-65~200	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 100mA; I_B= 0	60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	60		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1.5A; I_B= 0.15A		1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1.5A; I_B= 0.15A		1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 1.5A; V_{CE}= 5V		1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 60V; I_B= 0		0.1	mA
I_{CEX}	Collector Cutoff Current	V_{CE}= 60V; V_{BE}= -1.5V V_{CE}= 60V; V_{BE}= -1.5V; T_C= 150℃		0.1 2.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0		1.0	mA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	15		
h_{FE-2}	DC Current Gain	I_C= 3A; V_{CE}= 5V	5		